

Automotive-grade high voltage ignition coil driver NPN power Darlington transistor

Datasheet - production data

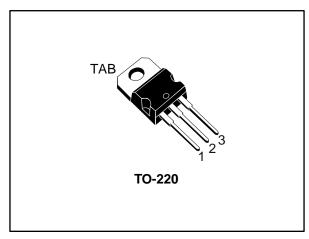
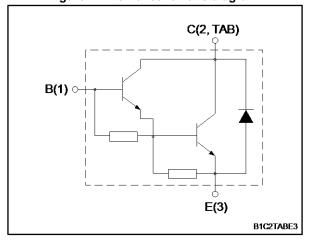


Figure 1: Internal schematic diagram



Features



- AEC-Q101 qualified
- Very rugged Bipolar technology
- High operating junction temperature

Applications

• High ruggedness electronic ignitions

Description

This is a high voltage power Darlington transistor developed using multi-epitaxial planar technology. It has been properly designed for automotive environment as electronic ignition power actuators.

Table 1: Device summary

Order code	Marking	Package	Packing
BU931T	BU931T	TO-220	Tube

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Contents BU931T

BU931T Electrical ratings

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
Vces	Collector-emitter voltage (V _{BE} = 0)	500	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	400	V
V _{EBO}	Emitter-base voltage (I _C = 0)	5	V
Ic	Collector current	10	Α
I _{CM}	Collector peak current	20	Α
lΒ	Base current	1	Α
Івм	Base peak current	5	Α
Ртот	P _{TOT} Total dissipation at Tc = 25 °C		W
T _{stg}	Storage temperature range	CE to 475	°C
Tj	Operating junction temperature range	-65 to 175	°C

Table 3: Thermal data

Symbol	Parameter	Value	Unit
RthJC	Thermal resistance junction-case	1.2	°C/W
R _{thJA}	Thermal resistance junction-ambient	62.5	°C/W

Electrical characteristics BU931T

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4: Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
	Collector out off	V _{BE} = 0 V, V _{CE} = 500 V		-	100	μA
I CUIT C IIL		$V_{BE} = 0 \text{ V}, V_{CE} = 500 \text{ V},$ $T_{C} = 125 ^{\circ}\text{C}^{(1)}$		1	0.5	mA
	Collector cut-off	I _B = 0 A, V _{CE} = 450 V		ı	100	μΑ
ICEO	current	$I_B = 0 \text{ A}, \text{ V}_{CE} = 450 \text{ V},$ $T_C = 125 ^{\circ}\text{C}^{(1)}$		-	0.5	mA
I _{EBO}	Emitter cut-off current	I _C = 0 A, V _{EB} = 5 V		-	20	mA
V _{CEO(sus)} ⁽²⁾	Collector-emitter sustaining voltage	I _B = 0 A, I _C = 100 mA	400	1		V
	Collector-emitter saturation voltage	I _C = 7 A, I _B = 70 mA		ı	1.6	V
V _{CE(sat)} ⁽²⁾		Ic = 8 A, I _B = 100 mA		1	1.8	V
		Ic = 10 A, I _B = 250 mA		-	1.8	V
	Base-emitter saturation voltage	$I_C = 7 \text{ A}, I_B = 70 \text{ mA}$		-	2.2	V
V _{BE(sat)} ⁽²⁾		Ic = 8 A, I _B = 100 mA		ı	2.4	V
		I _C = 10 A, I _B = 250 mA		-	2.5	V
h _{FE} ⁽²⁾	DC current gain	Ic = 5 A, VcE = 10 V	300	-		
VF	Diode forward voltage	I _F = 10 A		-	2.5	V
Functional test		V _{CC} = 24 V,L = 7 mH, V _{clamp} = 400 V (see <i>Figure 10: "Functional test circuit"</i>)	8	-		А

Notes:

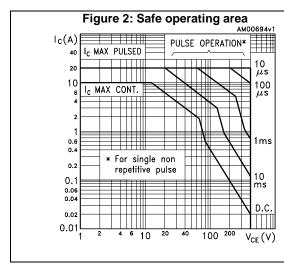
Table 5: Inductive load switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
ts	Storage time	Vcc = 12 V, V _{clamp} = 300 V, L = 7 mH,	-	15	-	μs
t _f	Fall time	R_{BE} = 47 Ω , I_C = 7 A, I_B = 70 mA	-	0.5	-	μs

 $[\]ensuremath{^{(1)}}\mbox{Defined}$ by design, not subject to production test.

 $^{^{(2)}\}text{Pulse}$ test: pulse duration ≤ 300 µs, duty cycle ≤ 2 %.

2.1 Electrical characteristics (curves)



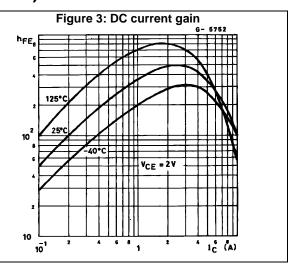
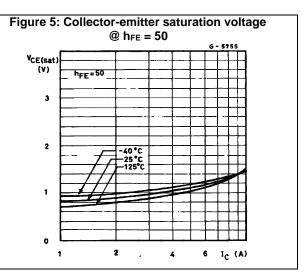


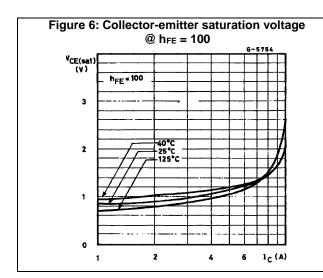
Figure 4: Switching time inductive load

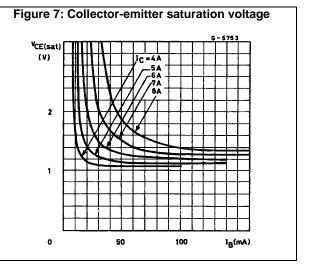
(µs)

10

Vct. =300V
Vcc =12V
hrE =100
ReE=470hm
L =7mH
Tcose =25°C





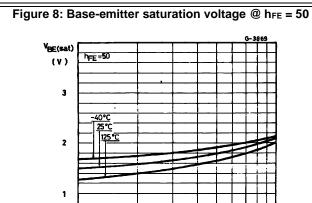


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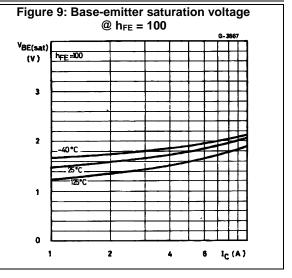


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I_C (A)

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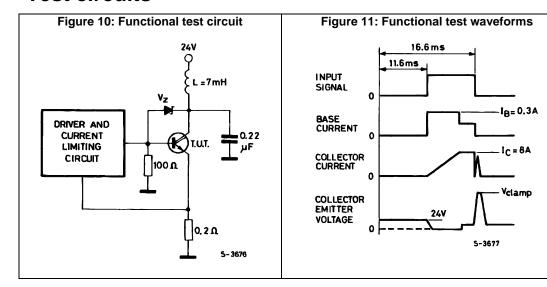


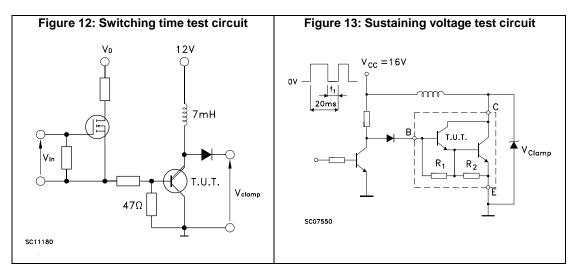
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BU931T Test circuits

3 Test circuits





Package information BU931T

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

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BU931T Package information

4.1 TO-220 type A package information

Figure 14: TO-220 type A package outline

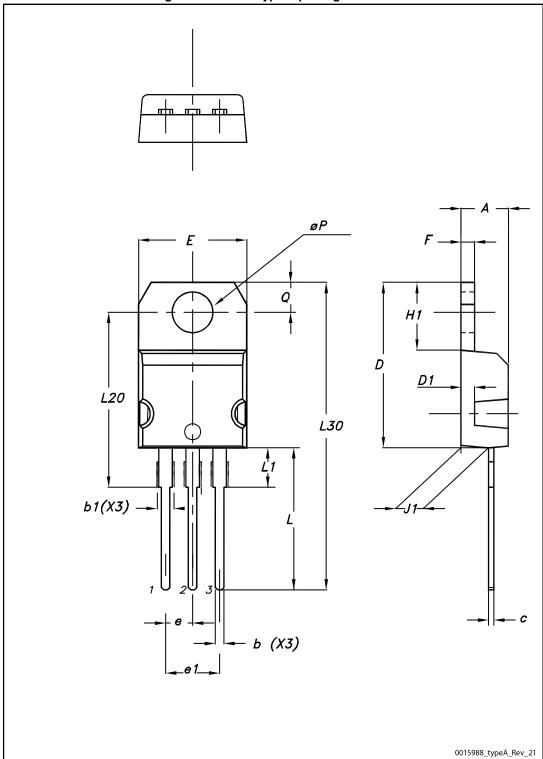


Table 6: TO-220 type A package mechanical data

Dim		mm	
Dim.	Min.	Тур.	Max.
А	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
С	0.48		0.70
D	15.25		15.75
D1		1.27	
Е	10.00		10.40
е	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øΡ	3.75		3.85
Q	2.65		2.95

BU931T Revision history

5 Revision history

Table 7: Document revision history

Date	Revision	Changes
18-Nov-2008 3		Package changed from TO-218 to TO-247 for BU931P. Inserted type in TO-220 (BU931T).
02-Dec-2009	4	Modified Ic test condition value of V _{CEO(sus)} parameter <i>Table 4 on page 4</i> , updated TO-220 package mechanical data.
12-Oct-2017	5	The part numbers BU931 and BU931P have been moved to two separate datasheets. Modified Table 2: "Absolute maximum ratings", Table 3: "Thermal data" and Table 4: "Electrical characteristics". Updated Section 4: "Package information". Minor text changes.



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